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SHEET 1 OF 2

FORM PTO - 1449				ATTORNEY DOCKET NO.: WPG-001					
INFORMATION DISCLOSURE STATEMENT				APPLICANT(S): Chang et al.					
				SERIAL NO.: 10/715,743					
				FILING DATE: 11/17/03 GROUP: Not Yet Assigned					
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
AKS	A1	6,143,626	11/07/00	Yabu et al.					
	A2	5,918,142	06/29/99	Park et al.					
	A3	5,834,346	11/10/98	Sun et al.					
	A4	5,759,886	06/02/98	Chung					
	A5	5,728,627	03/17/98	Nam et al.					
	A6	5,716,891	02/10/98	Kodama					
	A7	5,552,342	09/03/96	Itou et al.					
	A8	5,006,480	04/09/91	Chang et al.					
	A9	4,935,380	06/19/90	Okumura					
	A10	4,830,974	05/16/89	Chang et al.					
	A11	4,824,767	04/25/89	Chambers et al.					
AKS	A12	4,363,830	12/14/82	Hsu et al.					
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
AKS	C1	Formation of submicron T-gate by rapid thermally reflowed resist with metal transfer layer, C.C. Meng, G.R. Liao and S.S. Lu: ELECTRONICS LETTERS, Vol. 37 No. 16 (2001) pp. 1045-1046.							
AKS	C2	Thermal Flow and Chemical Shrink Techniques for Sub-100 nm Contact Hole Fabrication in Electron Beam Lithography, Hsuen-Li Chen, Fu-Hsiang Ko, Lung-Sheng Li, Chien-Kui Hsu, Ben-Chang Chen and Tieh-Chi Chu: Jpn. J. Appl. Phys. Vol. 41 (2002) pp. 4163-4166.							
AKS	C3	Fabrication of 0.2 μ m Gate Pseudomorphic Inverted Hemt By Phase-Shifting Technology, H.T. Yamada, R. Shigemasa, H.I. Fujihira, S. Nishi and T. Saito: Solid State Electronics Vol. 38, No. 9 pp. 1631-1634, 1995.							

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OTHER ART, JOURNAL ARTICLES, ETC.		
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AKS	C4	30-nm-Gate InP-Based Lattice-Matched High Electron Mobility Transistors with 350 GHz Cutoff Frequency, T. Suemitsu, T. Ishii, H. Yokoyama, T. Enoki, Y. Ishii and T. Tamamura: Jpn. J. Appl. Phys. Vol. 38 (1999) pp. L154-156.
AKS	C5	Improved Recessed-Gate Structure for Sub-0.1- μ m-Gate InP-Based High Electron Mobility Transistors, T. Suemitsu, T. Enoki, H. Yokoyama and Y. Ishii: Jpn. J. Appl. Phys. Vol. 37 (1998) pp. 1365-1372.
AKS	C6	Ultra-Short 25-nm-Gate Lattice-Matched InAlAs/InGaAs HEMTs within the Range of 400 GHz Cutoff Frequency, Yoshimi Yamashita, Akira Endoh, Keisuke Shinohara, Masataka Higashiwaki, Kohki Hikosaka and Takashi Mimura: IEEE Electron Device Letters. Vol. 22 No. 8 (2001) 367-369.
EXAMINER	DATE CONSIDERED	
Asst. Examiner Sanhar	8/16/04	